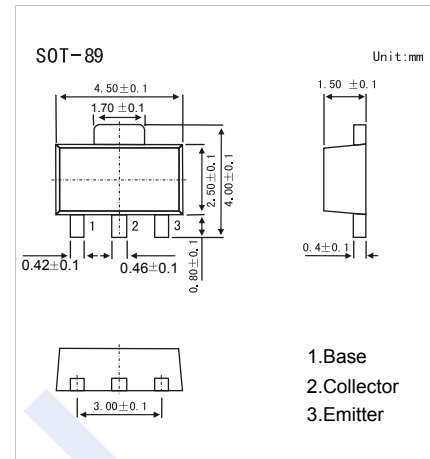


NPN Transistors

2SC2881-HF

■ Features

- Small Flat Package
- High Transition Frequency
- High Voltage
- Complementary to 2SA1201-HF
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	120	V
Collector - Emitter Voltage	V_{CE0}	120	
Emitter - Base Voltage	V_{EB0}	5	
Collector Current - Continuous	I_C	800	mA
Base Current	I_B	160	
Collector Power Dissipation	P_C	500	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = 100\mu\text{A}$, $I_E = 0$	120			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = 10\text{mA}$, $I_B = 0$	120			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100\mu\text{A}$, $I_C = 0$	5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 120\text{V}$, $I_E = 0$			0.1	uA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{V}$, $I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}$, $I_B = 50\text{mA}$			1	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500\text{mA}$, $I_B = 50\text{mA}$			1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = 5\text{V}$, $I_C = 0.5\text{A}$			1	
DC current gain	h_{FE}	$V_{CE} = 5\text{V}$, $I_C = 100\text{mA}$	80		240	
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$			30	pF
Transition frequency	f_T	$V_{CE} = 5\text{V}$, $I_C = 100\text{mA}$		120		MHz

■ Classification of h_{FE}

Type	2SC2881-O-HF	2SC2881-Y-HF
Range	80-160	120-240
Marking	CO* _F	CY* _F

NPN Transistors

2SC2881-HF

■ Typical Characteristics

